

2SC2636

Silicon NPN epitaxial planar type

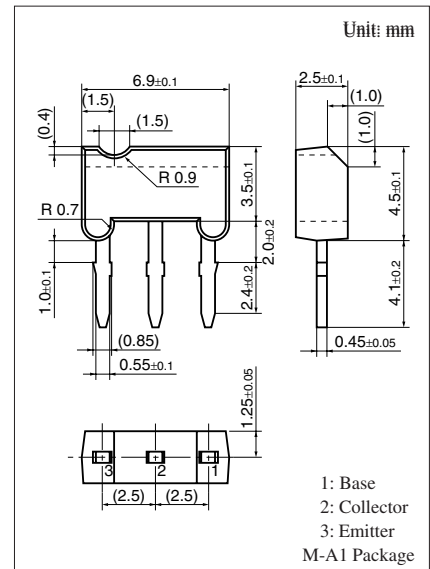
For high-frequency amplification/oscillation

■ Features

- High transition frequency f_T
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	30	V
Collector-emitter voltage (Base open)	V_{CEO}	20	V
Emitter-base voltage (Collector open)	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	400	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



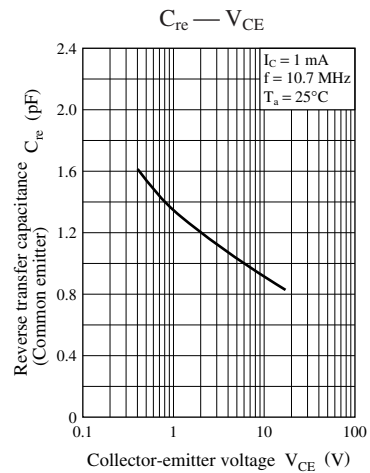
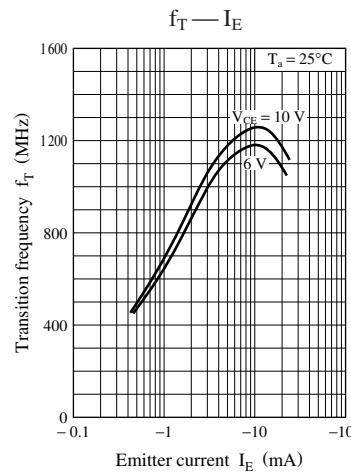
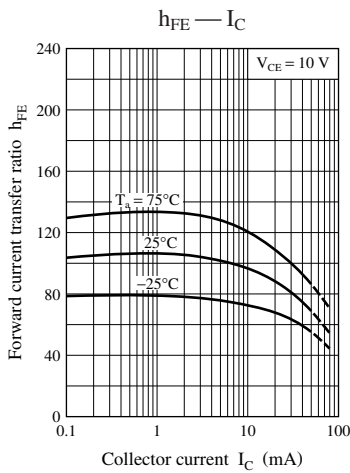
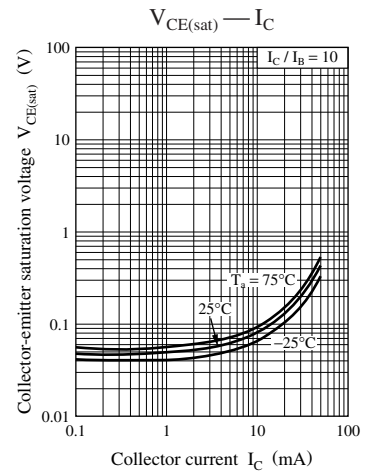
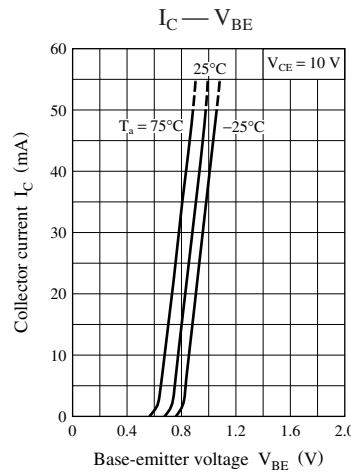
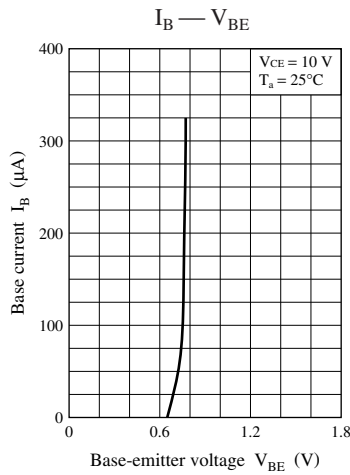
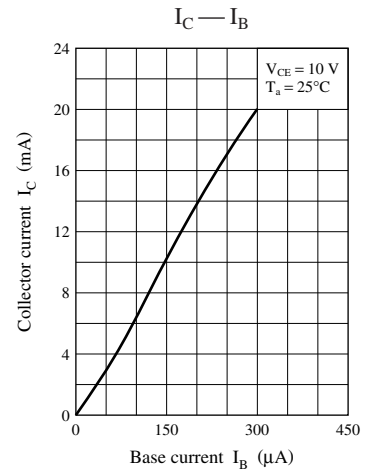
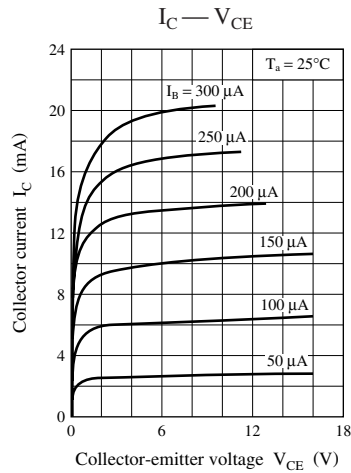
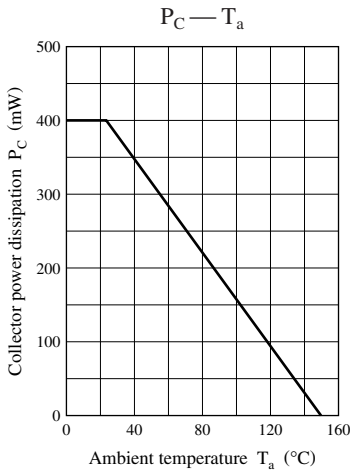
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

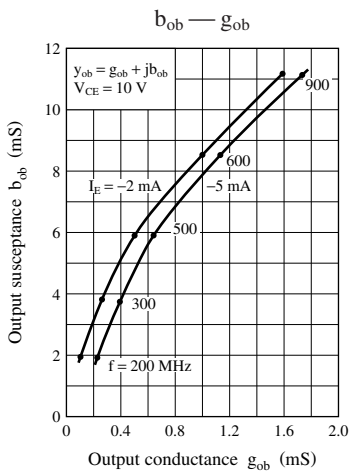
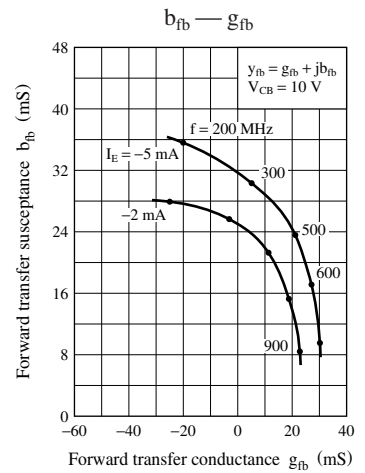
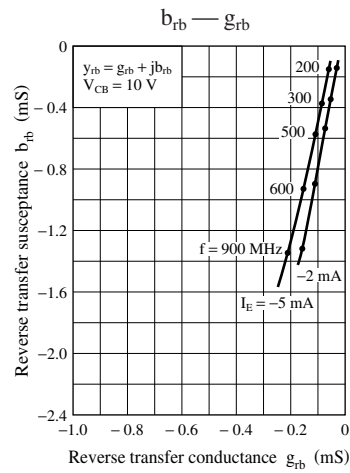
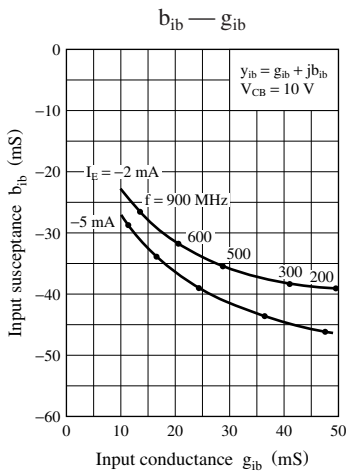
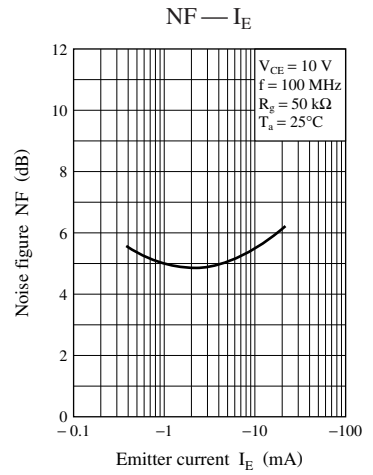
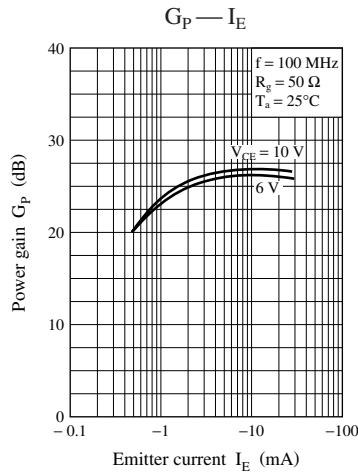
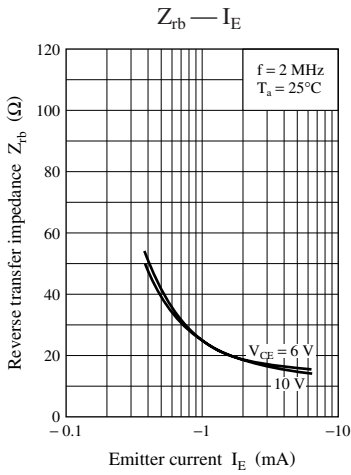
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 100 \mu\text{A}$, $I_E = 0$	30			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}$, $I_C = 0$	3			V
Base-emitter voltage	V_{BE}	$V_{CB} = 10 \text{ V}$, $I_E = -2 \text{ mA}$		720		mV
Forward current transfer ratio *	h_{FE}	$V_{CE} = 10 \text{ V}$, $I_C = 2 \text{ mA}$	25			—
Transition frequency	f_T	$V_{CB} = 10 \text{ V}$, $I_E = -15 \text{ mA}$, $f = 200 \text{ MHz}$	600	1200	1600	MHz
Power gain	G_P	$V_{CB} = 10 \text{ V}$, $I_E = -1 \text{ mA}$, $f = 100 \text{ MHz}$		20		dB
Reverse transfer capacitance (Common base)	C_{rb}	$V_{CB} = 6 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		0.8		pF
Reverse transfer capacitance (Common emitter)	C_{re}	$V_{CE} = 10 \text{ V}$, $I_C = 1 \text{ mA}$, $f = 10.7 \text{ MHz}$			1.5	pF
Collector-base parameter	$r_{bb}' \cdot C_C$	$V_{CB} = 10 \text{ V}$, $I_E = -10 \text{ mA}$, $f = 31.9 \text{ MHz}$			25	ps

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	T	S
h_{FE}	600 to 1300	900 to 1600





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